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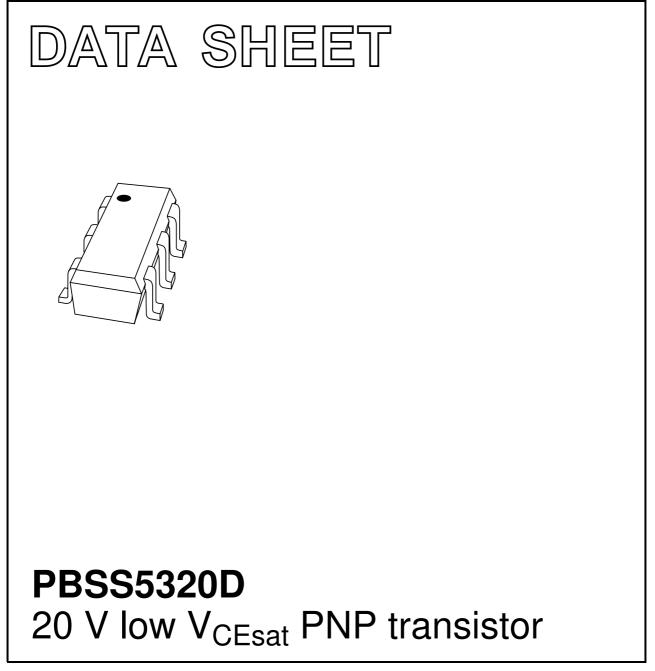
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet

2002 Jun 12



20 V low V_{CEsat} PNP transistor

FEATURES

- · Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

 PNP low $\mathsf{V}_{\mathsf{CEsat}}$ transistor in a SOT457 (SC-74) plastic package.

MARKING

TYPE NUMBER	MARKING CODE			
PBSS5320D	52			

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage -20 V		
I _C	collector current (DC)	-3	А
I _{CM}	peak collector current	-5	А
R _{CEsat}	equivalent on-resistance	133	mΩ

PINNING

PIN	DESCRIPTION	
1	collector	
2	collector	
3	base	
4	emitter	
5	collector	
6	collector	

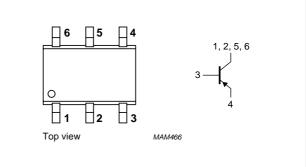


Fig.1 Simplified outline (SOT457; SC-74) and symbol.

PBSS5320D

20 V low V_{CEsat} PNP transistor

PBSS5320D

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-20	V
V _{CEO}	collector-emitter voltage	open base	—	-20	V
V _{EBO}	emitter-base voltage	open collector	—	-5	V
I _C	collector current (DC)		—	-3	А
I _{CM}	peak collector current		—	-5	А
Ι _Β	base current		-	-500	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	600	mW
		$T_{amb} \le 25 \ ^{\circ}C$; note 2	-	750	mW
T _{stg}	storage temperature		-65	+150	°C
Тj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board, single side copper, tinplated, mounting pad for collector 1 cm².
- 2. Device mounted on a printed-circuit board, single side copper, tinplated, mounting pad for collector 6 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	208	K/W
ambient	note 2	160	K/W	

Notes

- 1. Device mounted on a printed-circuit board, single side copper, tinplated, mounting pad for collector 1 cm².
- 2. Device mounted on a printed-circuit board, single side copper, tinplated, mounting pad for collector 6 cm².

20 V low V_{CEsat} PNP transistor

PBSS5320D

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -20 \text{ V}; \text{ I}_{E} = 0$	-	-	-100	nA
		$V_{CB} = -20 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -100 \text{ mA}$	200	-	-	
		$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	200	-	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -1000 \text{ mA}; \text{ note } 1$	200	-	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -2000 \text{ mA}; \text{ note } 1$	150	-	-	
V _{CEsat}	collector-emitter saturation	$I_{C} = -500 \text{ mA}; I_{B} = -5 \text{ mA}$	-	-	-130	mV
	voltage	$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}$	-	-	-80	mV
		$I_{\rm C} = -1$ A; $I_{\rm B} = -50$ mA	-	-	-160	mV
		$I_{C} = -2 \text{ A}; I_{B} = -20 \text{ mA}; \text{ note } 1$	-	-	-400	mV
		$I_{C} = -2 \text{ A}; I_{B} = -200 \text{ mA}; \text{ note } 1$	-	-	-250	mV
		$I_{C} = -3$ A; $I_{B} = -300$ mA; note 1	-	-	-400	mV
R _{CEsat}	equivalent on-resistance	$I_{C} = -3$ A; $I_{B} = -300$ mA; note 1	-	85	133	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_{C} = -2$ A; $I_{B} = -200$ mA; note 1	-	_	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -1 \text{ A}; \text{ note } 1$	-1.2	_	_	V
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	-	_	50	pF
F _T	transition frequency	$I_{C} = -200 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 100 MHz	100	_	_	MHz

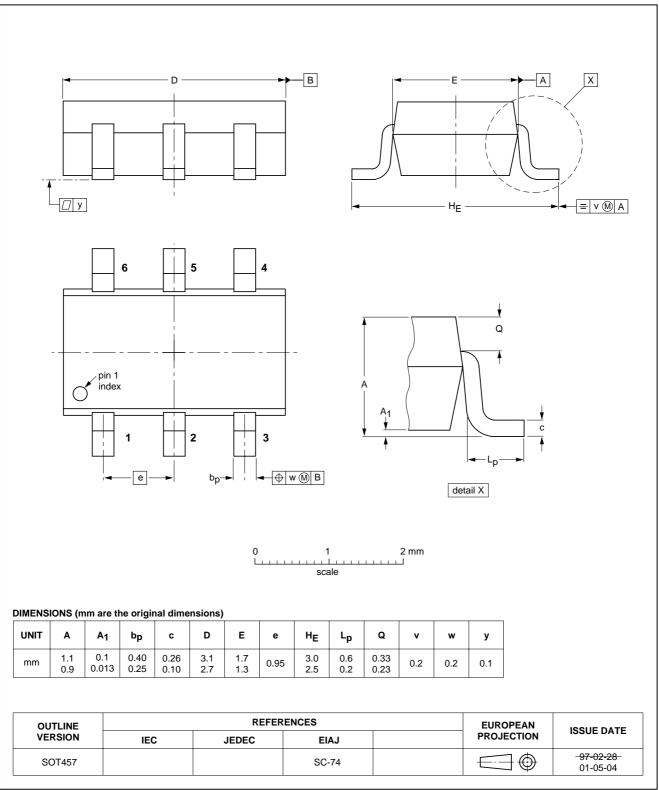
Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

20 V low V_{CEsat} PNP transistor

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads



PBSS5320D

SOT457

20 V low V_{CEsat} PNP transistor

PBSS5320D

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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